PNP/NPN Epitaxial Planar Silicon Darlington Transistor



# 2SB1228/2SD1830

# **Driver Applications**

## **Applications**

 Suitable for use in control of motor drivers, printer hammer drivers, relay drivers, and constant-voltage regulators.

#### **Features**

- · High DC current gain.
- · Large current capacity and wide ASO.
- · Low saturation voltage.
- · Micaless package facilitating mounting.

(): 2SB1228

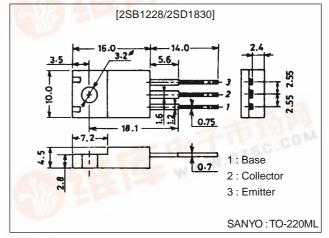
## **Specifications**

#### Absolute Maximum Ratings at Ta = 25°C

# **Package Dimensions**

unit:mm

2041A



Parameter	Symbol	Conditions	Ratings	Unit
Collector-to-Base Voltage	V <sub>CBO</sub>		(–)110	V
Collector-to-Emitter Voltage	VCEO		(-)100	V
Emitter-to-Base Voltage	V <sub>EBO</sub>		(-)6	V
Collector Current	I <sub>C</sub>		(-)8	Α
Collector Current (Pulse)	I <sub>CP</sub>	1 to	(–)12	Α
Collector Dissipation	PC	AND LIFE ISSUED	2.0	W
		Tc=25°C	30	W
Junction Temperature	Tj		150	°C
Storage Temperature	Tstg	O Lin	-55 to +150	°C

#### Electrical Characteristics at Ta = 25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	Offit
Collector Cutoff Current	I <sub>CBO</sub>	V <sub>CB</sub> =(-)80V, I <sub>E</sub> =0			(-)0.1	mA
Emitter Cutoff Current	I <sub>EBO</sub>	V <sub>EB</sub> =(-)5V, I <sub>C</sub> =0			(-)3.0	mA
DC Current Gain	hFE	V <sub>CE</sub> =(-)3V, I <sub>C</sub> =(-)4A	1500	4000		100
Gain-Bandwidth Product	fT	V <sub>CE</sub> =(-)5V, I <sub>C</sub> =(-)4A		20	50.	MHz
Collector-to-Emitter Saturation Voltage	VCE(sat)	I <sub>C</sub> =(-)4A, I <sub>B</sub> =(-)8mA	and All	0.9	(–)1.5	V
		477 717 1-1		(-1.0)		V
Base-to-Emitter Saturation Voltage	V <sub>BE(sat)</sub>	I <sub>C</sub> =(-)4A, I <sub>B</sub> =(-)8mA			(-)2.0	V

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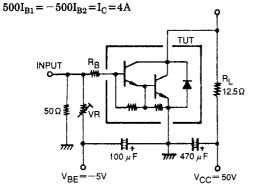
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Parameter	Symbol	Conditions		Ratings		
	Symbol		min	typ	max	Unit
Collector-to-Base Breakdown Voltage	V(BR)CBO	I <sub>C</sub> =(-)5mA, I <sub>E</sub> =0	(–)110			V
Collector-to-Emitter Breakdown Voltage	V <sub>(BR)</sub> CEO	I <sub>C</sub> =(-)50mA, R <sub>BE</sub> =∞	(–)100			V
Turn-ON Time	ton	See specified Test Circuit		0.6		μs
				(0.7)		μs
Storage Time	t <sub>stg</sub>	See specified Test Circuit		4.8		μs
				(1.4)		μs
Fall Time	t <sub>f</sub>	See specified Test Circuit		1.6		μs
				(1.5)		μs

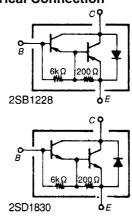
#### **Switching Time Test Circuit**

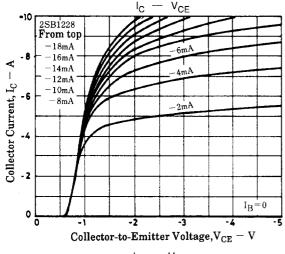
PW =  $50\mu s$ , Duty cycle  $\leq 1\%$ 

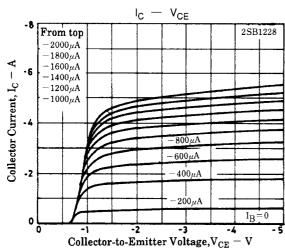


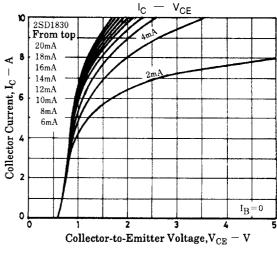
(For PNP, the polarity is reversed.)

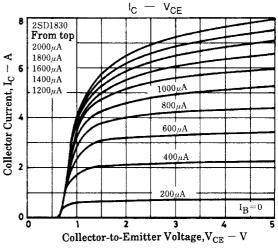
#### **Electrical Connection**



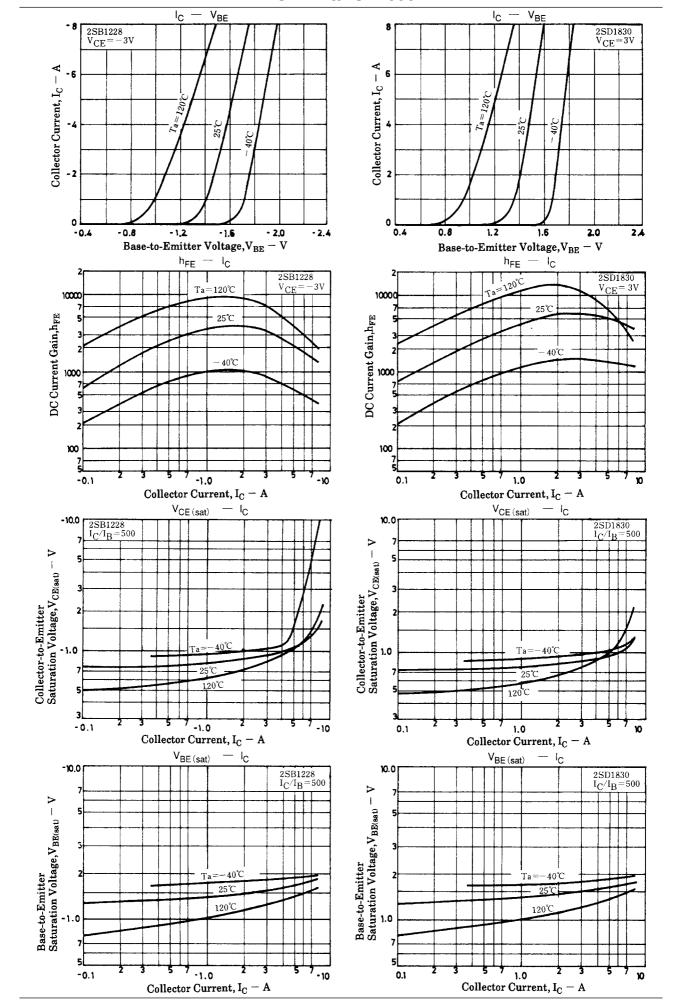




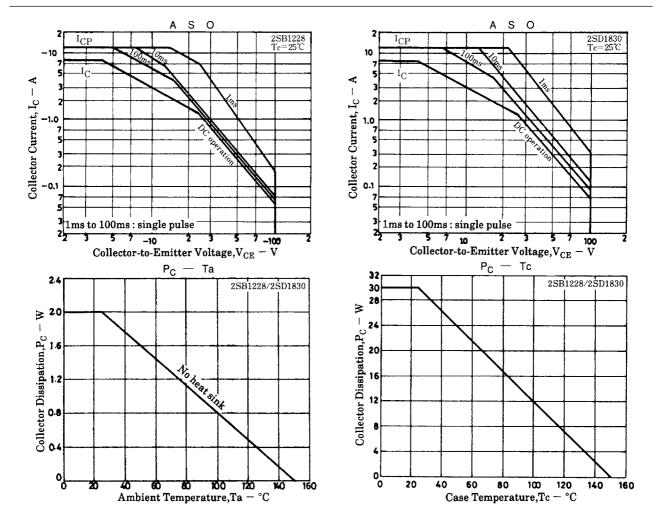




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